

a pressure detecting means provided inside said upper electrode, wherein operation of said parallel-plate dry-etching apparatus ceases if a pressure measured by said pressure detecting means is lower than a predetermined value.

5. (Twice Amended) An apparatus for manufacturing a semiconductor device, comprising:

an upper electrode that supplies gas in a parallel-plate dry etching apparatus;
a first pressure detecting means provided inside of said upper electrode;
a second pressure detecting means provided within said dry etching apparatus in

which a wafer is placed; and

a detecting means which measures a pressure differential between respective pressures of said first and said second pressure detecting means, and upon reaching a predetermined pressure differential, operation of the apparatus is terminated.

REMARKS

Status of the Claims

Upon entry of the present amendment, claims 1-9 will be pending in this application. Claims 3 and 5 are the independent claims.

Objection to the Drawings

The proposed amendment to Fig. 2 in red ink is believed to bring it in compliance with MPEP § 608.02(g). A similar amendment was submitted on July 15, 2002. Apparently this was not satisfactory. In the event that the present proposed changes are